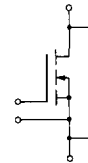
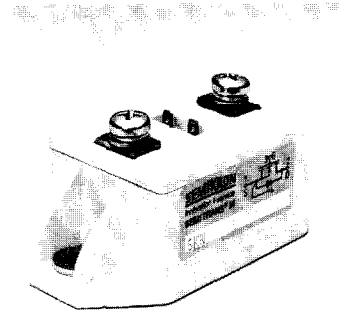


## SEMITRANS® M Power MOSFET Modules SKM 191



Absolute Maximum Ratings		Values	Units
Symbol	Conditions <sup>1)</sup>		
V <sub>DS</sub>		1000	V
V <sub>DGR</sub>	R <sub>GS</sub> = 20 kΩ	1000	V
I <sub>D</sub>		28	A
I <sub>DM</sub>		112	A
V <sub>GS</sub>		± 20	V
P <sub>D</sub>		700	W
T <sub>j</sub> , T <sub>stg</sub>		-55 ... +150	°C
V <sub>isol</sub>	AC, 1 min, 200 μA	2 500	V
humidity	DIN 40 040	Class F	
climate	DIN IEC 68 T.1	55/150/56	
Inverse Diode			
I <sub>F</sub> = - I <sub>D</sub>		28	A
I <sub>FM</sub> = - I <sub>DM</sub>		112	A

Characteristics		min.	typ.	max.	Units
Symbol	Conditions <sup>1)</sup>				
V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = 0,25 mA	1000	-	-	V
V <sub>GS(th)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 1 mA	2,1	3,0	4,0	V
I <sub>DSS</sub>	V <sub>GS</sub> = 0, } T <sub>j</sub> = 25 °C V <sub>DS</sub> = 1000 V } T <sub>j</sub> = 125 °C	-	50	250	μA
I <sub>GSS</sub>	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0	-	10	100	nA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 18 A	-	380	370	mΩ
g <sub>is</sub>	V <sub>DS</sub> = 25 V, I <sub>D</sub> = 18 A	15	22	-	S
C <sub>CHC</sub>	per MOSFET	-	-	160	pF
C <sub>iss</sub>	V <sub>GS</sub> = 0	-	22	30	nF
C <sub>oss</sub>	V <sub>DS</sub> = 25 V	-	1	1,5	nF
C <sub>rss</sub>	f = 1 MHz	-	0,48	0,8	nF
L <sub>DS</sub>		-	-	20	nH
I <sub>d(on)</sub>	V <sub>DD</sub> = 500 V	-	60	-	ns
t <sub>r</sub>	I <sub>D</sub> = 18 A	-	30	-	ns
I <sub>d(off)</sub>	V <sub>GS</sub> = 10 V	-	350	-	ns
t <sub>f</sub>	R <sub>GS</sub> = 3,3 Ω	-	60	-	ns
Inverse Diode					
V <sub>SD</sub>	I <sub>F</sub> = 56 A, V <sub>GS</sub> = 0	-	1,15	1,4	V
t <sub>rr</sub>	T <sub>j</sub> = 25 °C <sup>2)</sup>	-	2000	-	ns
	T <sub>j</sub> = 150 °C <sup>2)</sup>	-	-	-	ns
Q <sub>rr</sub>	T <sub>j</sub> = 25 °C <sup>2)</sup>	-	30	-	μC
	T <sub>j</sub> = 150 °C <sup>2)</sup>	-	-	-	
Thermal Characteristics					
R <sub>thjc</sub>		-	-	0,18	°C/W
R <sub>thch</sub>	M <sub>1</sub> , surface 10 μm	-	-	0,05	°C/W

Mechanical Data		4	-	6	Nm
Symbol	Description				
M <sub>1</sub>	to heatsink, SI Units				
	to heatsink, US Units	35	-	53	lb.in.
M <sub>2</sub>	for terminals, SI Units	2,5	-	3,5	Nm
	for terminals, US Units	22	-	24	lb.in.
a		-	-	5x9,81	m/s <sup>2</sup>
w		-	-	150	g
Case	→ page B 6 - 69			D 15	

<sup>1)</sup> T<sub>case</sub> = 25 °C, unless otherwise specified.

<sup>2)</sup> I<sub>F</sub> = - I<sub>D</sub>, V<sub>R</sub> = 100 V, - di<sub>F</sub>/dt = 100 A/μs

### Features

- N Channel, enhancement mode
- Short internal connections avoid oscillations
- Switching kW's in less than 1 μs
- Isolated copper baseplate
- All electrical connections on top for easy busbaring
- Large clearances and creepage distances
- UL recognized, file no. E 63 532

### Typical Applications

- Switched mode power supplies
- DC servo and robot drives
- DC choppers
- Resonant and welding inverters
- AC motor drives
- Laser power supplies
- UPS equipment
- Plasma cutting
- Not suitable for linear amplification

**This is an electrostatic discharge sensitive device (ESDS). Please observe the international standard IEC 747-1, Chapter IX.**

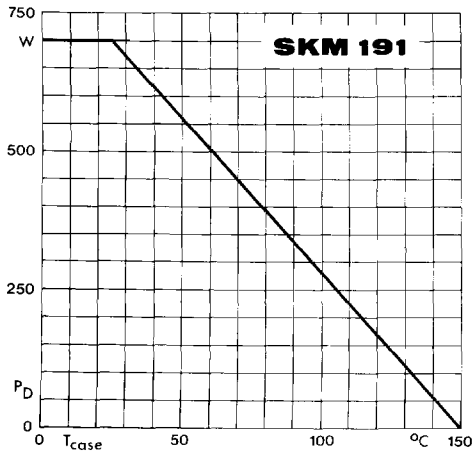


Fig. 1 Rated power dissipation vs. temperature

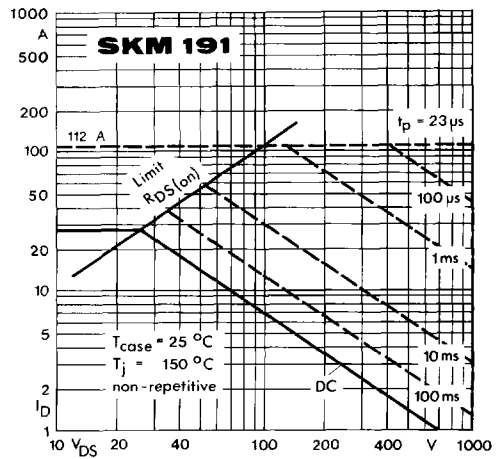


Fig. 2 Maximum safe operating area

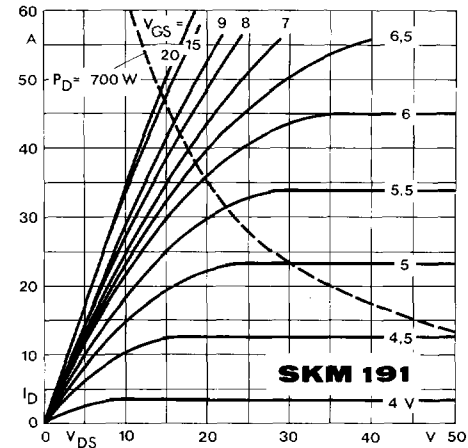


Fig. 3 Output characteristic

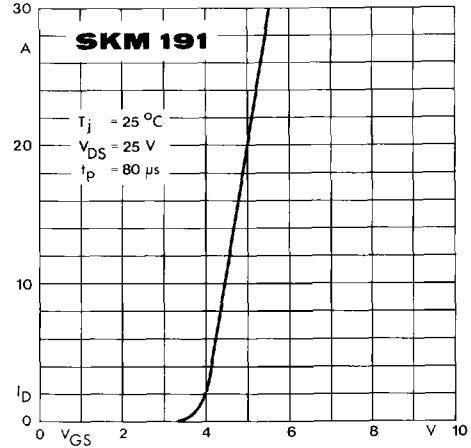


Fig. 4 Transfer characteristic

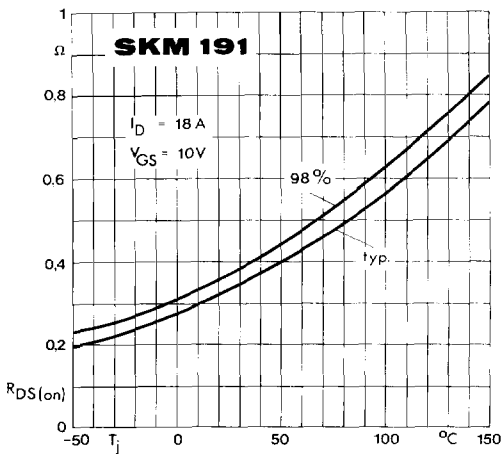


Fig. 5 On-resistance vs. temperature

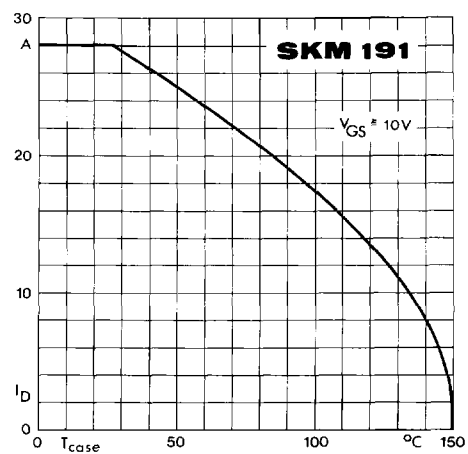


Fig. 6 Rated current vs. temperature

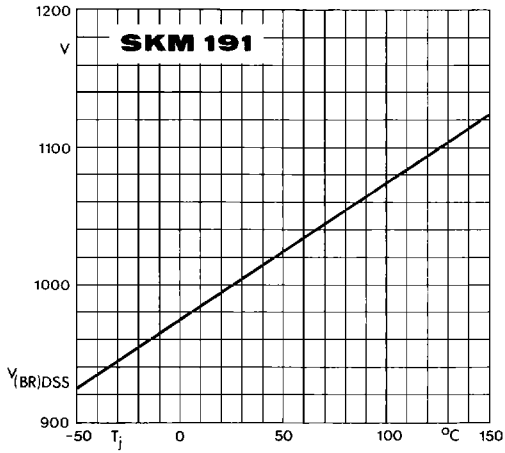


Fig. 7 Breakdown voltage vs. temperature

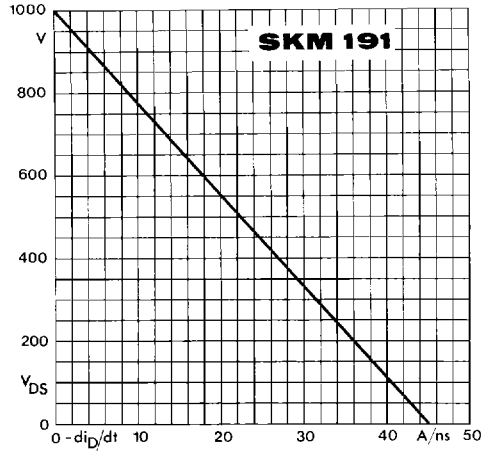


Fig. 8 Drain-source voltage derating

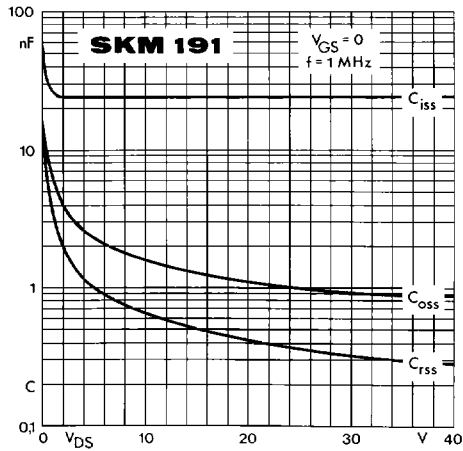


Fig. 9 Capacitances vs. drain-source voltage

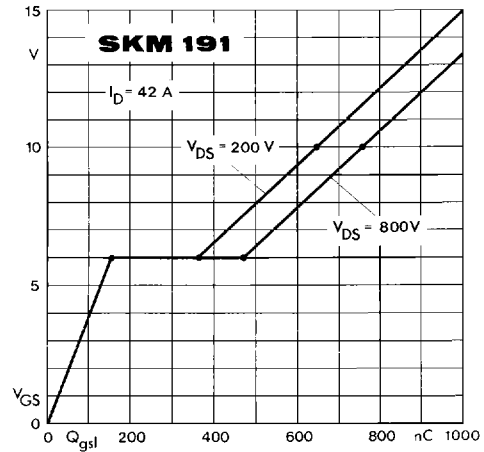


Fig. 10 Gate charge characteristic

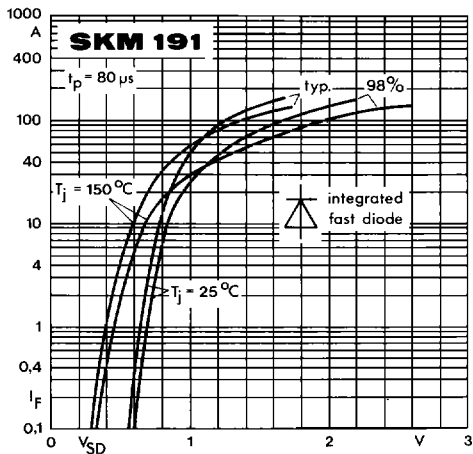


Fig. 11 Diode forward characteristic

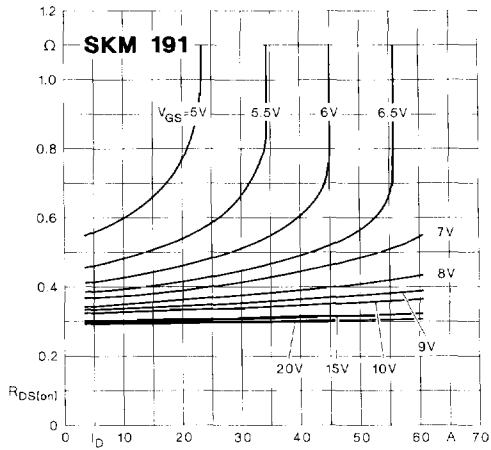


Fig. 13 On-resistance vs. drain current

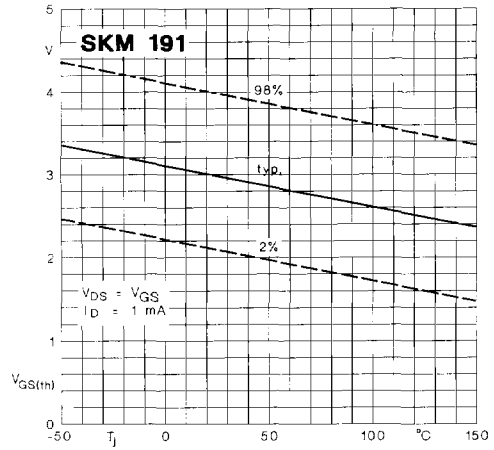


Fig. 14 Gate-source threshold voltage

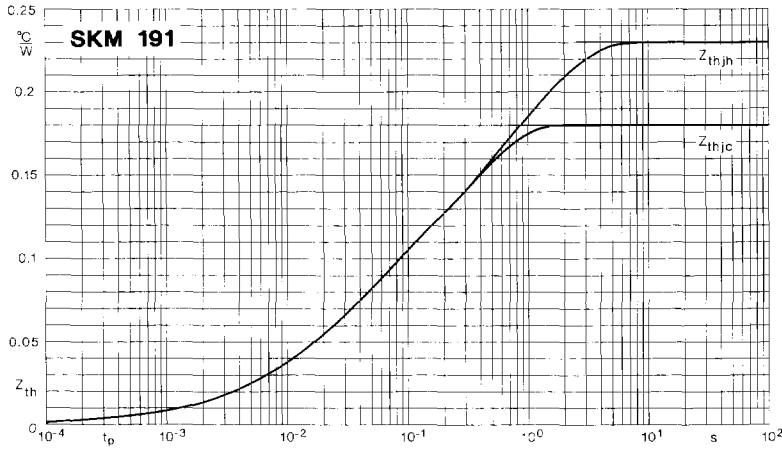


Fig. 51 Transient thermal impedance

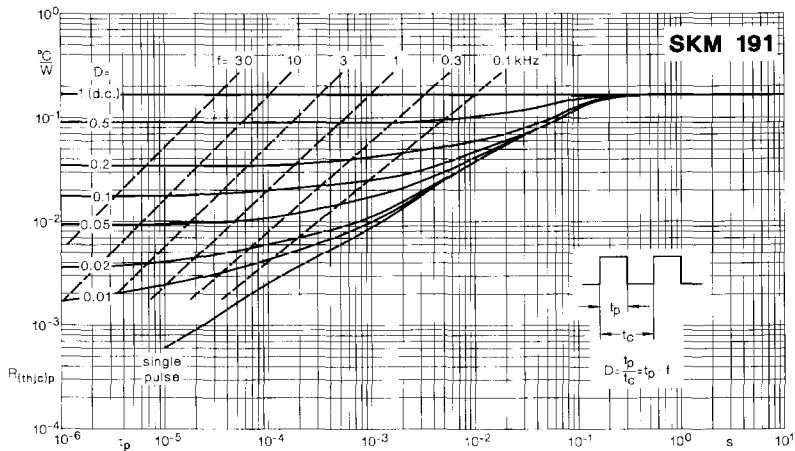


Fig. 52 Thermal impedance under pulse conditions